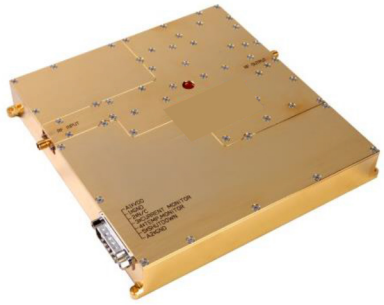
HD31878
SOLID STATE HIGH POWER AMPLIFIER



FEATURES

Class AB linear GaAsFET design
Designed for narrow bandwidth Ka-Band applications
Suitable for all single channel modulations standards
Built-in protection circuits
High reliability and ruggedness

ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	25 ±0.1 GHz	
Power Output Psat	10 Watt Typ	CW
Power Output @ P1dB	8 Watt Min	
Power Gain	40 dB Min	
Power Gain Flatness	1.0 dB p-p Max	Constant input power
Input Return Loss	10 dB Min	Relative to 50 Ohm
Harmonics	>30 dBc Typ	At Rated Pout
Non Harmonics Spurious	>60 dBc	
Operating Voltage	9 VDC	
Current Consumption	18 Amp Max	At rated Pout
Max Input Power	+3 dBm	Without damage
Load VSWR Protection	5 : 1	

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +65 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non Condensation

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions L x W x H	160 X 190 X 27 mm	Excluding Connectors
Weight	TBD	Max Weight
RF Connectors In/Out	H-Type female	
DC Power / Interface Connector	7-Pin Hybrid D-Sub	
Cooling	External Heatsink	Forced air required

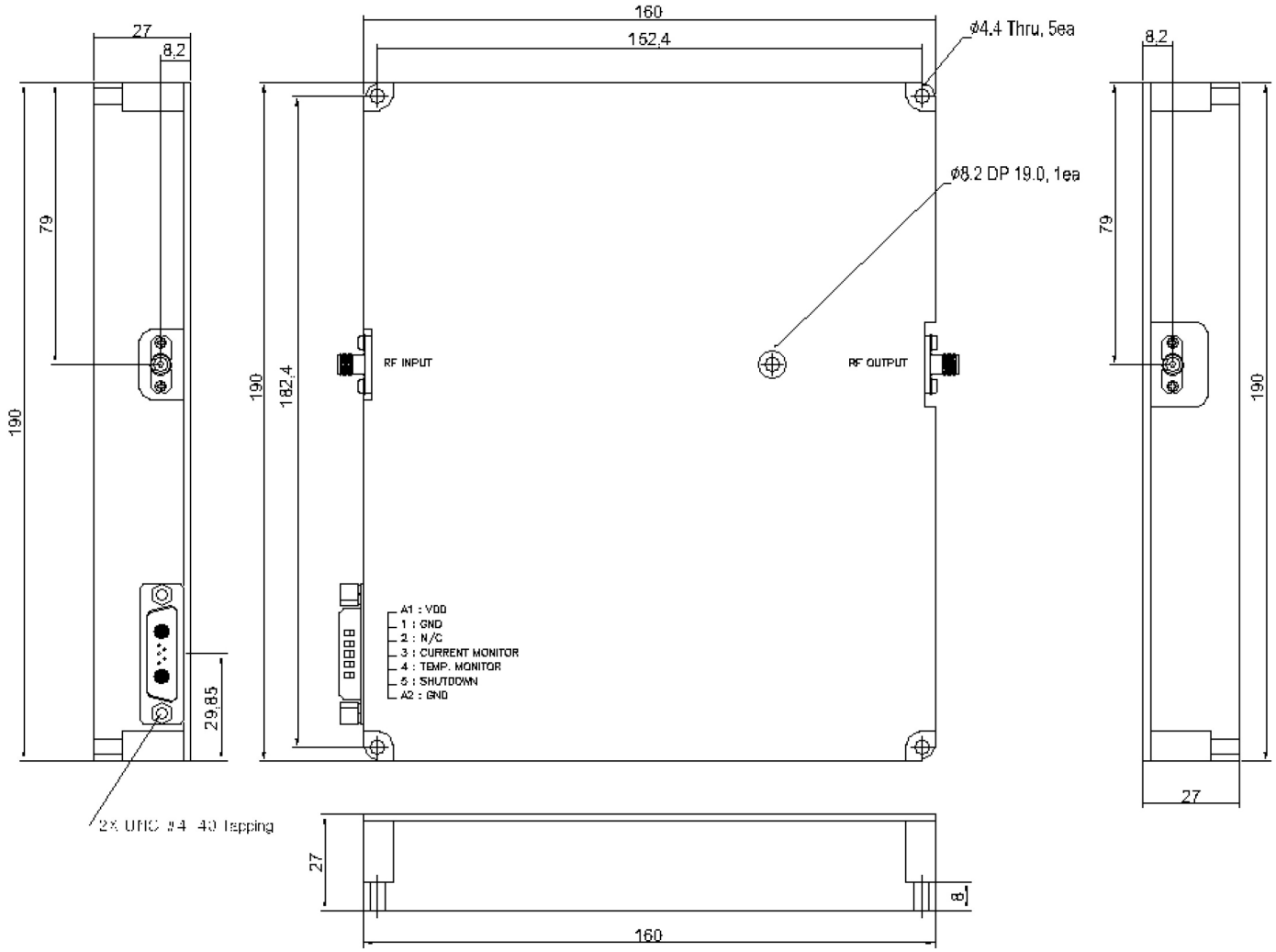
D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	FWD	N/C
2	REV	N/C
3	CURRENT SENSOR	I_D@20mV/100mA Typ
4	TEMP SENSOR	V_T@10mV/°C + 500mV Typ
5	SHUTDOWN	TTL
A1	VDD	9VDC
A2	GND	Ground

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OUTLINE DRAWING



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